

2SD1253, 2SD1253A

Silicon NPN triple diffusion planar type

For power amplification

Complementary to 2SB930 and 2SB930A

Features

- High forward current transfer ratio h_{FE} which has satisfactory linearity
- Low collector to emitter saturation voltage $V_{CE(sat)}$
- N type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Rated	Unit
Collector to base voltage	V_{CBO}	60	V
2SD1253A		80	
Collector to emitter voltage	V_{CEO}	60	V
2SD1253A		80	
Emitter to base voltage	V_{EBO}	5	V
Peak collector current	I_{CP}	8	A
Collector current	I_C	4	A
Collector power dissipation	P_C	$T_C=25^\circ\text{C}$	40
		$T_a=25^\circ\text{C}$	1.3
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	2SD1253	I_{CES}			400	μA
	2SD1253A				400	
Collector cutoff current	2SD1253	I_{CEO}	$V_{CE} = 30\text{V}, I_B = 0$		700	μA
	2SD1253A				700	
Emitter cutoff current	I_{EBO}	$V_{EB} = 5\text{V}, I_C = 0$			1	mA
Collector to emitter voltage	2SD1253	V_{CEO}	$I_C = 30\text{mA}, I_B = 0$	60		V
	2SD1253A			80		
Forward current transfer ratio		h_{FE1}^*	$V_{CE} = 4\text{V}, I_C = 1\text{A}$	40		250
		h_{FE2}	$V_{CE} = 4\text{V}, I_C = 3\text{A}$	15		
Base to emitter voltage	V_{BE}	$V_{CE} = 4\text{V}, I_C = 3\text{A}$			2	V
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 4\text{A}, I_B = 0.4\text{A}$			1.5	V
Transition frequency	f_T	$V_{CE} = 5\text{V}, I_C = 0.5\text{A}, f = 1\text{MHz}$		20		MHz
Turn-on time	t_{on}	$I_C = 4\text{A}, I_{B1} = 0.4\text{A}, I_{B2} = -0.4\text{A}, V_{CC} = 50\text{V}$		0.4		μs
Storage time	t_{stg}			1.2		μs
Fall time	t_f			0.5		μs

* h_{FE1} Rank classification

Rank	R	Q	P
h_{FE1}	40 to 90	70 to 150	120 to 250



